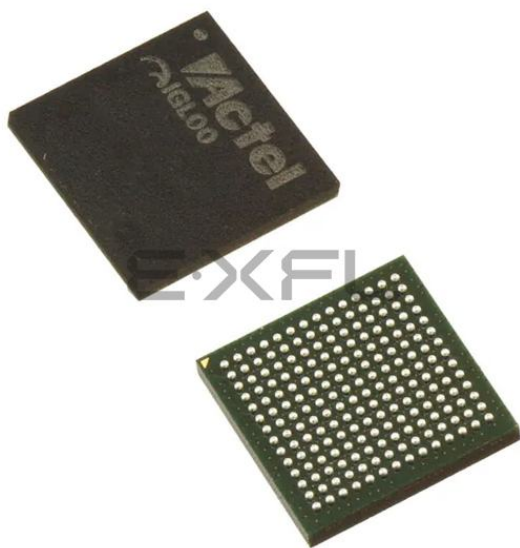




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

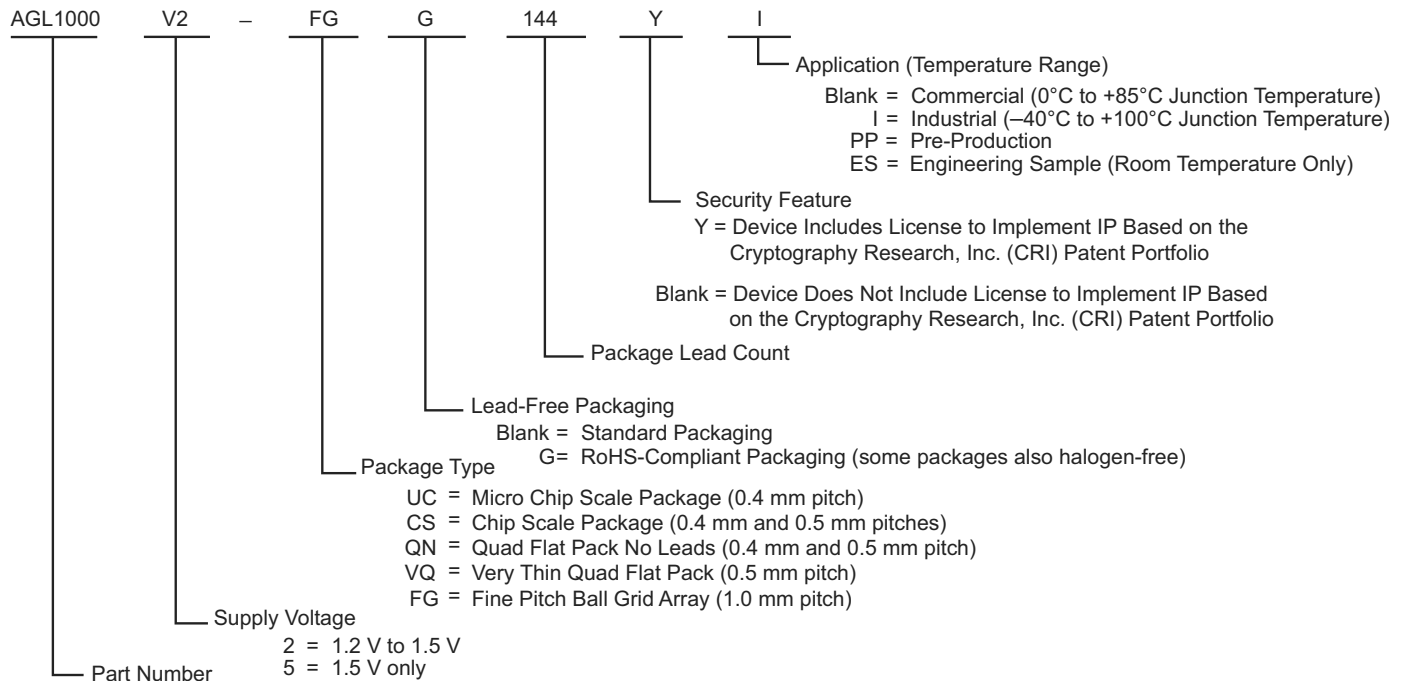
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	9216
Total RAM Bits	55296
Number of I/O	143
Number of Gates	400000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl400v2-csg196

IGLOO Ordering Information



IGLOO Devices

AGL015 = 15,000 System Gates
AGL030 = 30,000 System Gates
AGL060 = 60,000 System Gates
AGL125 = 125,000 System Gates
AGL250 = 250,000 System Gates
AGL400 = 400,000 System Gates
AGL600 = 600,000 System Gates
AGL1000 = 1,000,000 System Gates

IGLOO Devices with Cortex-M1

M1AGL250 = 250,000 System Gates
M1AGL600 = 600,000 System Gates
M1AGL1000 = 1,000,000 System Gates

Note: Marking Information: IGLOO V2 devices do not have V2 marking, but IGLOO V5 devices are marked accordingly.

**Table 2-21 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power ($\mu\text{W}/\text{MHz}$)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	4.978	3.982	3.892	2.854	2.845	1.751	0.000	0.000
PAC2	Clock contribution of a Global Spine	2.773	2.248	1.765	1.740	1.122	1.261	2.229	2.229
PAC3	Clock contribution of a VersaTile row	0.883	0.924	0.881	0.949	0.939	0.962	0.942	0.942
PAC4	Clock contribution of a VersaTile used as a sequential module	0.096	0.095	0.096	0.095	0.095	0.096	0.094	0.094
PAC5	First contribution of a VersaTile used as a sequential module	0.045							
PAC6	Second contribution of a VersaTile used as a sequential module	0.186							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.158	0.149	0.158	0.157	0.160	0.170	0.160	0.155
PAC8	Average contribution of a routing net	0.756	0.729	0.753	0.817	0.678	0.692	0.738	0.721
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.10							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

**Table 2-22 • Different Components Contributing to the Static Power Consumption in IGLOO Device
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Static Power (mW)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PDC1	Array static power in Active mode	See Table 2-12 on page 2-9.							
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-8.							
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.							
PDC4	Static PLL contribution	0.90							
PDC5	Bank quiescent power (VCCI-Dependent)	See Table 2-12 on page 2-9.							
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PDC7	I/O output pin static power (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Microsemi Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-23 on page 2-19.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-24 on page 2-19.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-24 on page 2-19. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = (P_{DC1} \text{ or } P_{DC2} \text{ or } P_{DC3}) + N_{BANKS} * P_{DC5} + N_{INPUTS} * P_{DC6} + N_{OUTPUTS} * P_{DC7}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1} , P_{AC2} , P_{AC3} , and P_{AC4} are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Table 2-33 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case V_{CCI} (per standard)
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
3.3 V LVCMOS Wide Range ²	100 μA	8	High	5	–	0.97	2.62	0.18	1.17	0.66	2.63	2.02	2.79	3.17	ns
2.5 V LVCMOS	8 mA	8	High	5	–	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
1.8 V LVCMOS	4 mA	4	High	5	–	0.97	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	ns
1.5 V LVCMOS	2 mA	2	High	5	–	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Detailed I/O DC Characteristics

Table 2-37 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	$V_{IN} = 0$, $f = 1.0$ MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	$V_{IN} = 0$, $f = 1.0$ MHz		8	pF

Table 2-38 • I/O Output Buffer Maximum Resistances¹
Applicable to Advanced I/O Banks

Standard	Drive Strength	$R_{PULL-DOWN}$ (Ω) ²	$R_{PULL-UP}$ (Ω) ³
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
1.2 V LVCMOS ⁴	2 mA	158	164
1.2 V LVCMOS Wide Range ⁴	100 μ A	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on V_{CCI} , drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / I_{OL_{spec}}$
3. $R_{(PULL-UP-MAX)} = (V_{CCI_{max}} - VOH_{spec}) / I_{OH_{spec}}$
4. Applicable to IGLOO V2 Devices operating at $V_{CCI} \geq V_{CC}$

Table 2-42 • I/O Short Currents IOSH/IOSL
Applicable to Advanced I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 μ A	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: * $T_J = 100^{\circ}\text{C}$

Applies to 1.2 V Core Voltage**Table 2-89 • 2.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
4 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
6 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
8 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
12 mA	Std.	1.55	4.17	0.26	1.20	1.10	4.23	3.99	3.30	3.67	10.02	9.77	ns
16 mA	Std.	1.55	3.98	0.26	1.20	1.10	4.04	3.88	3.34	3.76	9.83	9.66	ns
24 mA	Std.	1.55	3.90	0.26	1.20	1.10	3.96	3.90	3.40	4.09	9.75	9.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-90 • 2.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
4 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
6 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
8 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
12 mA	Std.	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
16 mA	Std.	1.55	2.59	0.26	1.20	1.10	2.63	2.24	3.34	3.88	8.41	8.03	ns
24 mA	Std.	1.55	2.60	0.26	1.20	1.10	2.64	2.18	3.40	4.22	8.42	7.97	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-91 • 2.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
 Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
4 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
6 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
8 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
12 mA	Std.	1.55	3.66	0.26	1.19	1.10	3.71	3.55	2.94	3.41	9.50	9.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-111 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	6	6	32	39	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	8	8	66	55	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12	66	55	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-112 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Timing Characteristics**1.5 V DC Core Voltage****Table 2-115 • 1.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.62	0.18	1.17	0.66	6.75	6.06	2.79	2.31	10.35	9.66	ns
4 mA	Std.	0.97	5.75	0.18	1.17	0.66	5.86	5.34	3.06	2.78	9.46	8.93	ns
6 mA	Std.	0.97	5.43	0.18	1.17	0.66	5.54	5.19	3.12	2.90	9.13	8.78	ns
8 mA	Std.	0.97	5.35	0.18	1.17	0.66	5.46	5.20	2.63	3.36	9.06	8.79	ns
12 mA	Std.	0.97	5.35	0.18	1.17	0.66	5.46	5.20	2.63	3.36	9.06	8.79	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-116 • 1.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.97	0.18	1.17	0.66	3.04	2.90	2.78	2.40	6.63	6.50	ns
4 mA	Std.	0.97	2.60	0.18	1.17	0.66	2.65	2.45	3.05	2.88	6.25	6.05	ns
6 mA	Std.	0.97	2.53	0.18	1.17	0.66	2.58	2.37	3.11	3.00	6.18	5.96	ns
8 mA	Std.	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
12 mA	Std.	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-117 • 1.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	5.93	0.18	1.18	0.66	6.04	5.46	2.30	2.15	9.64	9.06	ns
4 mA	Std.	0.97	5.11	0.18	1.18	0.66	5.21	4.80	2.54	2.58	8.80	8.39	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-118 • 1.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.58	0.18	1.18	0.66	2.64	2.41	2.29	2.24	6.23	6.01	ns
4 mA	Std.	0.97	2.25	0.18	1.18	0.66	2.30	2.00	2.53	2.68	5.89	5.59	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer. Furthermore, all LVCMOS 1.2 V software macros comply with LVCMOS 1.2 V wide range as specified in the JESD8-12A specification.

Table 2-127 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-128 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-129 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
1 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

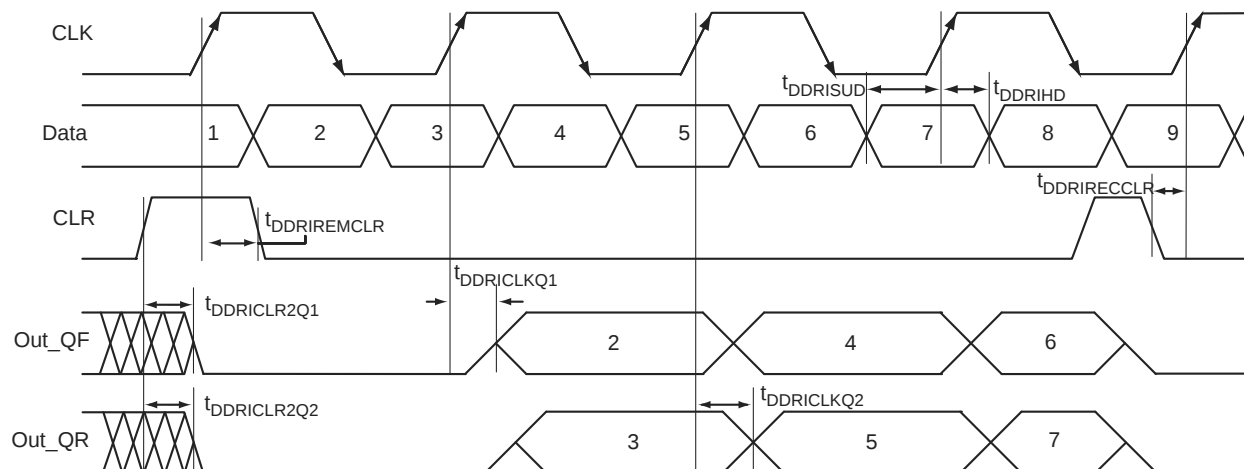


Figure 2-22 • Input DDR Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-164 • Input DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{DDRCLKQ1}	Clock-to-Out Out_QR for Input DDR	0.48	ns
t_{DDRCLKQ2}	Clock-to-Out Out_QF for Input DDR	0.65	ns
t_{DDRISUD1}	Data Setup for Input DDR (negedge)	0.50	ns
t_{DDRISUD2}	Data Setup for Input DDR (posedge)	0.40	ns
t_{DDRHD1}	Data Hold for Input DDR (negedge)	0.00	ns
t_{DDRHD2}	Data Hold for Input DDR (posedge)	0.00	ns
$t_{\text{DDRCLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.82	ns
$t_{\text{DDRCLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.98	ns
$t_{\text{DDRIREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{\text{DDRIRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.23	ns
t_{DDRIVCLR}	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

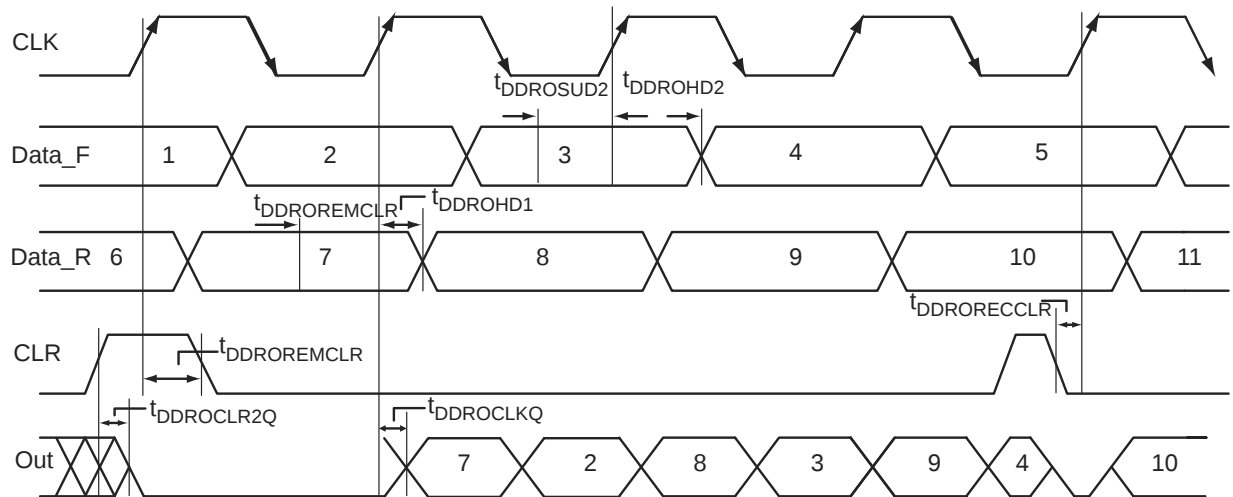


Figure 2-24 • Output DDR Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-167 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.07	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.67	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.67	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

JTAG Pins

IGLOO devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements. Refer to Table 3-2 for more information.

Table 3-2 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance ^{1,2}
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Notes:

1. The TCK pin can be pulled-up or pulled-down.
2. The TRST pin is pulled-down.
3. Equivalent parallel resistance if more than one device is on the JTAG chain

Table 3-3 • TRST and TCK Pull-Down Recommendations

VJTAG	Tie-Off Resistance*
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Note: Equivalent parallel resistance if more than one device is on the JTAG chain

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 3-2 and must satisfy the parallel resistance value requirement. The values in Table 3-2 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

CS196	
Pin Number	AGL400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO14RSB0
A6	IO18RSB0
A7	IO26RSB0
A8	IO29RSB0
A9	IO36RSB0
A10	GBC0/IO54RSB0
A11	GBB0/IO56RSB0
A12	GBB1/IO57RSB0
A13	GBA1/IO59RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO17RSB0
B7	IO25RSB0
B8	IO34RSB0
B9	IO39RSB0
B10	GND
B11	GBC1/IO55RSB0
B12	GBA0/IO58RSB0
B13	GBA2/IO60PPB1
B14	GBB2/IO61PDB1
C1	GAC2/IO153UDB3
C2	GAB2/IO154UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO15RSB0
C7	VCCIB0

CS196	
Pin Number	AGL400 Function
C8	IO31RSB0
C9	IO44RSB0
C10	IO49RSB0
C11	VCCIB0
C12	IO60NPB1
C13	GNDQ
C14	IO61NDB1
D1	IO153VDB3
D2	IO154VDB3
D3	GAA2/IO155UDB3
D4	IO150PPB3
D5	IO11RSB0
D6	IO20RSB0
D7	IO23RSB0
D8	IO28RSB0
D9	IO41RSB0
D10	IO47RSB0
D11	IO63PPB1
D12	VMV1
D13	IO62NDB1
D14	GBC2/IO62PDB1
E1	IO149PDB3
E2	GND
E3	IO155VDB3
E4	VCCIB3
E5	IO151USB3
E6	IO09RSB0
E7	IO12RSB0
E8	IO32RSB0
E9	IO46RSB0
E10	IO51RSB0
E11	VCCIB1
E12	IO63NPB1
E13	GND
E14	IO64PDB1
F1	IO149NDB3

CS196	
Pin Number	AGL400 Function
F2	IO144NPB3
F3	IO148PDB3
F4	IO148NDB3
F5	IO150NPB3
F6	IO07RSB0
F7	VCC
F8	VCC
F9	IO43RSB0
F10	IO73PDB1
F11	IO73NDB1
F12	IO66NDB1
F13	IO66PDB1
F14	IO64NDB1
G1	GFB1/IO146PDB3
G2	GFA0/IO145NDB3
G3	GFA2/IO144PPB3
G4	VCOMPLF
G5	GFC0/IO147NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO67NDB1
G11	GCB1/IO68PDB1
G12	GCA0/IO69NDB1
G13	IO72NDB1
G14	GCC2/IO72PDB1
H1	GFB0/IO146NDB3
H2	GFA1/IO145PDB3
H3	VCCPLF
H4	GFB2/IO143PPB3
H5	GFC1/IO147PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC

CS281	
Pin Number	AGL1000 Function
R15	IO122RSB2
R16	GDA1/IO113PPB1
R18	GDB0/IO112NPB1
R19	GDC0/IO111NPB1
T1	IO197PPB3
T2	GEC0/IO190NPB3
T4	GEB0/IO189NPB3
T5	IO181RSB2
T6	IO172RSB2
T7	IO171RSB2
T8	IO156RSB2
T9	IO159RSB2
T10	GND
T11	IO139RSB2
T12	IO138RSB2
T13	IO129RSB2
T14	IO123RSB2
T15	GDC2/IO116RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO112PPB1
U1	IO193PDB3
U2	GEA1/IO188PPB3
U6	IO167RSB2
U14	IO128RSB2
U18	TRST
U19	GDA0/IO113NPB1
V1	IO193NDB3
V2	VCCIB3
V3	GEC2/IO185RSB2
V4	IO182RSB2
V5	IO175RSB2
V6	GND
V7	IO161RSB2
V8	IO143RSB2
V9	IO146RSB2

CS281	
Pin Number	AGL1000 Function
V10	IO145RSB2
V11	IO144RSB2
V12	IO134RSB2
V13	IO133RSB2
V14	GND
V15	IO119RSB2
V16	GDA2/IO114RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO186RSB2
W3	IO183RSB2
W4	IO176RSB2
W5	IO170RSB2
W6	IO162RSB2
W7	IO157RSB2
W8	IO152RSB2
W9	IO149RSB2
W10	VCCIB2
W11	IO140RSB2
W12	IO135RSB2
W13	IO130RSB2
W14	IO125RSB2
W15	IO120RSB2
W16	IO118RSB2
W17	GDB2/IO115RSB2
W18	TCK
W19	GND

QN48	
Pin Number	AGL030 Function
1	IO82RSB1
2	GEC0/IO73RSB1
3	GEA0/IO72RSB1
4	GEB0/IO71RSB1
5	GND
6	VCCIB1
7	IO68RSB1
8	IO67RSB1
9	IO66RSB1
10	IO65RSB1
11	IO64RSB1
12	IO62RSB1
13	IO61RSB1
14	FF/IO60RSB1
15	IO57RSB1
16	IO55RSB1
17	IO53RSB1
18	VCC
19	VCCIB1
20	IO46RSB1
21	IO42RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO38RSB0
30	GDB0/IO34RSB0
31	GDA0/IO33RSB0
32	GDC0/IO32RSB0
33	VCCIB0
34	GND
35	VCC
36	IO25RSB0

QN48	
Pin Number	AGL030 Function
37	IO24RSB0
38	IO22RSB0
39	IO20RSB0
40	IO18RSB0
41	IO16RSB0
42	IO14RSB0
43	IO10RSB0
44	IO08RSB0
45	IO06RSB0
46	IO04RSB0
47	IO02RSB0
48	IO00RSB0

FG484	
Pin Number	AGL1000 Function
Y7	IO174RSB2
Y8	VCC
Y9	VCC
Y10	IO154RSB2
Y11	IO148RSB2
Y12	IO140RSB2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1

Revision	Changes	Page
Revision 19 (continued)	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO devices via an IEEE 1532 JTAG interface" (SAR 28756).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 21281).	1-8
	Values for VCCPLL at 1.2 V –1.5 V DC core supply voltage were revised in Table 2-2 • Recommended Operating Conditions 1 (SAR 22356). The value for VPUMP operation was changed from "0 to 3.45 V" to "0 to 3.6 V" (SAR 25220). The value for VCCPLL 1.5 V DC core supply voltage was changed from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 26551). The notes in the table were renumbered in order of their appearance in the table (SAR 21869).	2-2
	The temperature used in EQ 2 was revised from 110°C to 100°C for consistency with the limits given in Table 2-2 • Recommended Operating Conditions 1. The resulting maximum power allowed is thus 1.28 W. Formerly it was 1.71 W (SAR 26259).	2-6
	Values for CS196, CS281, and QN132 packages were added to Table 2-5 • Package Thermal Resistivities (SARs 26228, 32301).	2-6
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated to remove the column for –20°C and shift the data over to correct columns (SAR 23041).	2-7
	The tables in the "Quiescent Supply Current" section were updated with revised notes on IDD (SAR 24112). Table 2-8 • Power Supply State per Mode is new.	2-7
	The formulas in the table notes for Table 2-41 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 21348).	2-37
	The row for 110°C was removed from Table 2-45 • Duration of Short Circuit Event before Failure. The example in the associated paragraph was changed from 110°C to 100°C. Table 2-46 • I/O Input Rise Time, Fall Time, and Related I/O Reliability1 was revised to change 110° to 100°C. (SAR 26259).	2-40
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-28, 2-47, 2-77
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-56
	The values for F _{DDRIMAX} and F _{DDOMAX} were updated in the tables in the "Input DDR Module" section and "Output DDR Module" section (SAR 23919).	2-94, 2-97
	The following notes were removed from Table 2-147 • Minimum and Maximum DC Input and Output Levels (SAR 29428): ±5% Differential input voltage = ±350 mV	2-81
	Table 2-189 • IGLOO CCC/PLL Specification and Table 2-190 • IGLOO CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Mircosemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-115

Revision / Version	Changes	Page
Advance v0.7 (continued)	The former Table 2-16 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in IGLOO Devices (maximum drive strength and high slew selected) was removed.	N/A
	The "During Flash*Freeze Mode" section was updated to include information about the output of the I/O to the FPGA core.	2-57
	Table 2-31 • Flash*Freeze Pin Location in IGLOO Family Packages (device-independent) was updated to add UC81 and CS281. Flash*Freeze pins were assigned for CS81, CS121, and CS196.	2-61
	Figure 2-40 • Flash*Freeze Mode Type 2 – Timing Diagram was updated to modify the LSICC Signal.	2-55
	Information regarding calculation of the quiescent supply current was added to the "Quiescent Supply Current" section.	3-6
	Table 3-8 • Quiescent Supply Current (I_{DD}) Characteristics, IGLOO Flash*Freeze Mode [†] was updated.	3-6
	Table 3-9 • Quiescent Supply Current (I_{DD}) Characteristics, IGLOO Sleep Mode ($V_{CC} = 0\text{ V}$) [†] was updated.	3-6
	Table 3-11 • Quiescent Supply Current (I_{DD}), No IGLOO Flash*Freeze Mode ¹ was updated.	3-7
	Table 3-115 • Minimum and Maximum DC Input and Output Levels was updated.	3-58
	Table 3-156 • JTAG 1532 was updated and Table 3-155 • JTAG 1532 is new.	3-104
	The "121-Pin CSP" and "281-Pin CSP" packages are new.	4-5, 4-7
	The "81-Pin CSP" table for the AGL030 device was updated to change the G6 pin function to IO44RSB1 and the JG pin function to IO45RSB1.	4-4
	The "121-Pin CSP" table for the AGL060 device is new.	4-6
	The "256-Pin FBGA" table for the AGL1000 device is new.	4-34
	The "281-Pin CSP" table for the AGL 600 device is new.	4-8
	The "100-Pin VQFP" table for the AGL060 device is new.	4-18
	The "144-Pin FBGA" table for the AGL250 device is new.	4-24
	The "144-Pin FBGA" table for the AGL1000 device is new.	4-28
	The "484-Pin FBGA" table for the AGL600 device is new.	4-38
	The "484-Pin FBGA" table for the AGL1000 device is new.	4-43
Advance v0.6 (November 2007)	Table 1 • IGLOO Product Family, the "I/Os Per Package ¹ " table, and the "IGLOO Ordering Information", and the Temperature Grade Offerings table were updated to add the UC81 package.	i, ii, iii, iv
	The "81-Pin μ CSP" table for the AGL030 device is new.	4-3
	The "81-Pin CSP" table for the AGL030 device is new.	4-1
Advance v0.5 (September 2007)	Table 1 • IGLOO Product Family was updated for AGL030 in the Package Pins section to change CS181 to CS81.	i